

1. General Description

The EM74HC20; EM74HCT20 is a dual 4-input NAND gate. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

2. Features and Benefits

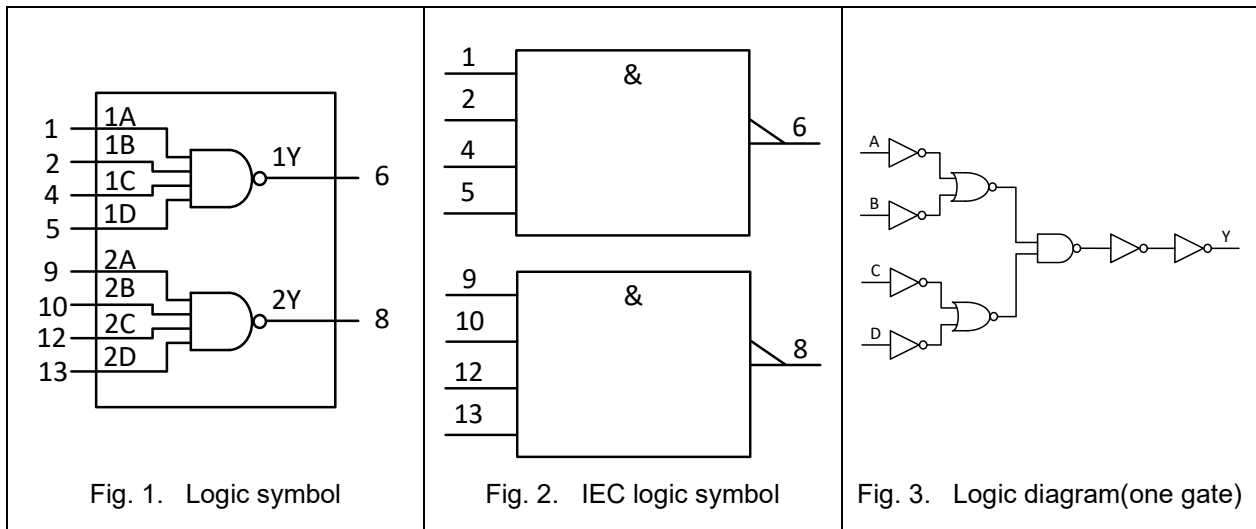
- Wide supply voltage range from 2.0 V to 6.0 V
- High noise immunity
- CMOS low power dissipation
- Latch-up performance exceeds 250 mA
- Complies with JEDEC standards:
 - JESD8C (2.7 V to 3.6 V)
 - JESD7A (2.0 V to 6.0 V)
- Input levels:
 - For EM74HC20: CMOS level
 - For EM74HCT20: TTL level
- ESD protection:
 - HBM ANSI/ESDA/JEDEC JS-001 Class 2 exceeds 3500 V
 - CDM ANSI/ESDA/JEDEC JS-002 Class C3 exceeds 2000 V
- Multiple package options

3. Ordering Information

Table 1. Ordering information

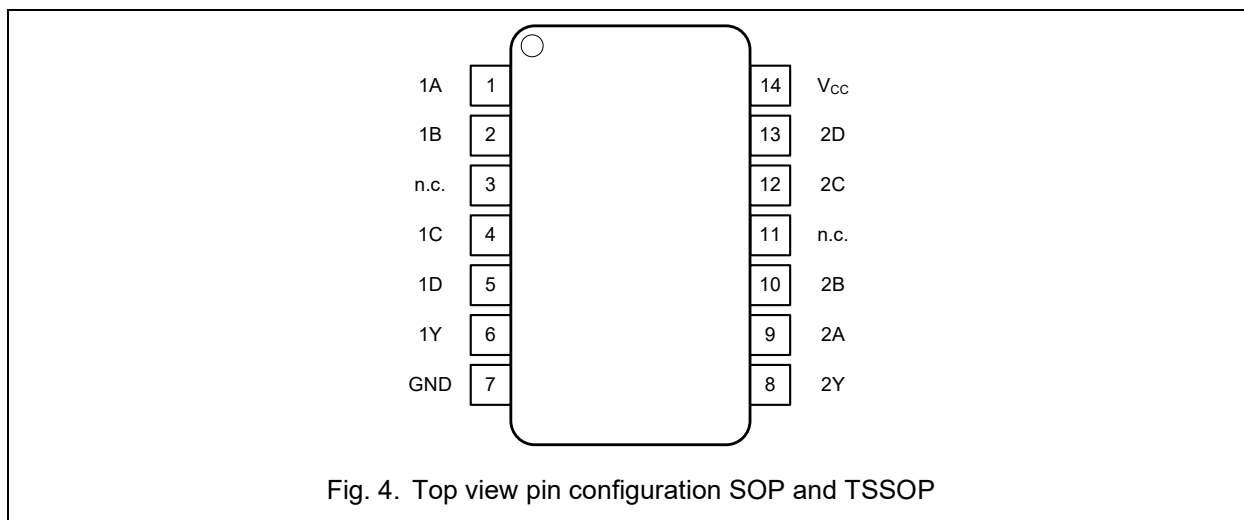
Type number	Package		
	Name	Description	Quantity
EM74HC20D	SOP-14L	plastic small outline package; 14 leads; body width 3.9 mm	3000
EM74HCT20D			
EM74HC20PW	TSSOP-14L	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	3000
EM74HCT20PW			

4. Function Diagram



5. Pinning Information

5.1. Pinning



5.2. Pin description

Table 2. Pin description

Symbol	Pin	Description
1A, 1B, 1C, 1D	1, 2, 4, 5	Data input
2A, 2B, 2C, 2D	9, 10, 12, 13	Data input
1Y, 2Y	6, 8	Data output
GND	7	Ground (0V)
V _{CC}	14	Supply voltage
n.c.	3, 11	Not connected

6.Functional Description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care.

Control				Output
nA	nB	nC	nD	nY
L	X	X	X	H
X	L	X	X	H
X	X	L	X	H
X	X	X	L	H
H	H	H	H	L

7.Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Table 4. Absolute Maximum Ratings

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND.

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$ [1]		± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$ [1]		± 20	mA
I_O	output current	$V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$		± 25	mA
I_{CC}	supply current			50	mA
I_{GND}	ground current		-50		mA
P_{tot}	total power dissipation			500	mW
T_{stg}	storage temperature		-65	150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

8. Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. EnergyMath does not recommend exceeding them or designing to Absolute Maximum Ratings.

Table 5. Recommended Operating Conditions

Symbol	Parameter	Conditions	EM74HC20			EM74HCT20			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0		V _{CC}	0		V _{CC}	V
V _O	output voltage		0		V _{CC}	0		V _{CC}	V
T _{amb}	ambient temperature		-40		125	-40		125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V _{CC} = 2.0 V			625				ns/V
		V _{CC} = 4.5 V		1.67	139		1.67	139	ns/V
		V _{CC} = 6.0 V			83				ns/V

EM74HC20; EM74HCT20

Dual 4-input NAND gate

9.Static Characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V). Typical values measured at $T_{amb} = 25^{\circ}\text{C}$ (unless otherwise noted).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
EM74HC20								
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5			1.5		V
		V _{CC} = 4.5 V	3.15			3.15		V
		V _{CC} = 6.0 V	4.2			4.2		V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V			0.5		0.5	V
		V _{CC} = 4.5 V			1.35		1.35	V
		V _{CC} = 6.0 V			1.8		1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = -20 μA; V _{CC} = 2.0 V	1.9			1.9		V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4			4.4		V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9			5.9		V
		I _O = -4.0 mA; V _{CC} = 4.5 V	3.84			3.7		V
		I _O = -5.2 mA; V _{CC} = 6.0 V	5.34			5.2		V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = 20 μA; V _{CC} = 2.0 V			0.1		0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V			0.1		0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V			0.1		0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V			0.33		0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V			0.33		0.4	V
I _I	input leakage current	V _I = V _{CC} or GND ; V _{CC} = 6.0 V			±1		±1	μA
I _{CC}	supply current	V _I = V _{CC} or GND ; I _O = 0 A ; V _{CC} = 6.0 V			20		40	μA
C _I	input capacitance			7				pF

EM74HC20; EM74HCT20

Dual 4-input NAND gate

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
EM74HCT20								
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0			2.0		V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V			0.8		0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V						
		I _O = -20 µA;	4.4		4.4		V	
		I _O = -4.0 mA;	3.84		3.7		V	
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V						
		I _O = 20 µA;			0.1		0.1	V
		I _O = 4.0 mA;			0.33		0.4	V
I _I	input leakage current	V _I = V _{CC} or GND ; V _{CC} = 5.5 V			±1		±1	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V			20		40	µA
ΔI _{CC}	additional supply current	per pin ; V _I = V _{CC} - 2.1 V; I _O = 0 A; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V			1.55		1.85	mA
C _I	input capacitance			10				pF

10. Dynamic Characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 6. Typical values measured at $T_{amb} = 25^{\circ}\text{C}$ (unless otherwise noted).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
EM74HC20								
t _{pd}	propagation delay	nA, nB, nC, nD to nY; see Fig. 5 [1]						
		V _{CC} = 2.0 V			35		40	ns
		V _{CC} = 4.5 V			20		25	ns
		V _{CC} = 6.0 V			15		20	ns
t _t	transition time	see Fig. 5 [2]						
		V _{CC} = 2.0 V			9		11	ns
		V _{CC} = 4.5 V			6		8	ns
		V _{CC} = 6.0 V			4		5	ns
C _{PD}	power dissipation capacitance	C _L = 15 pF; f = 1 MHz; V _I = GND to V _{CC} [3]		18				pF
EM74HCT20								
t _{pd}	propagation delay	nA, nB, nC, nD to nY; V _{CC} = 4.5 V; see Fig. 5 [1]			16		19	ns
t _t	transition time	V _{CC} = 4.5 V; see Fig. 5 [2]			6		8	ns
C _{PD}	power dissipation capacitance	C _L = 15 pF; f = 1 MHz; V _I = GND to (V _{CC} -1.5 V) [3]		37				pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH} .

[2] t_t is the same as t_{THL} and t_{TLH} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

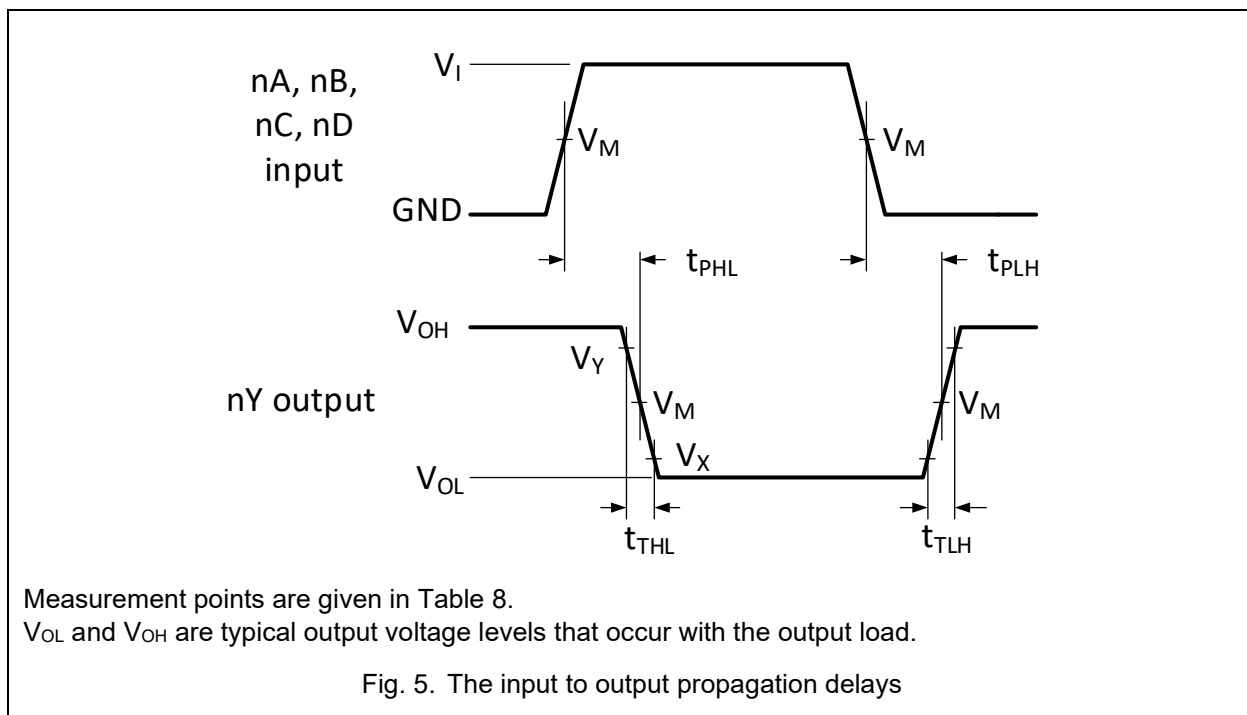
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

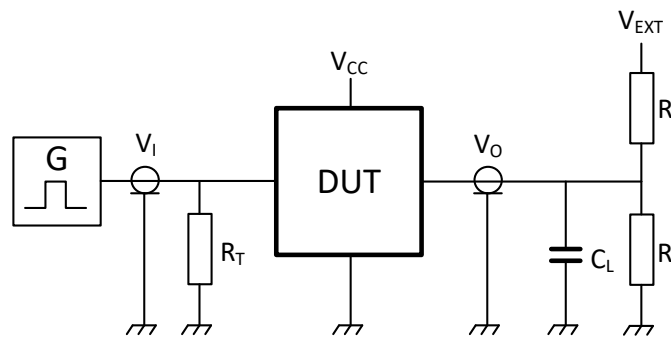
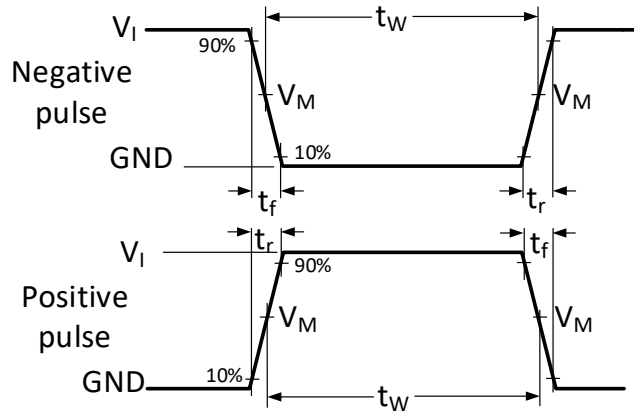
10.1. Waveforms and test circuit


Table 8. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
EM74HC20	$0.5V_{CC}$	$0.5V_{CC}$	$0.1V_{CC}$	$0.9V_{CC}$
EM74HCT20	1.3 V	1.3 V	$0.1V_{CC}$	$0.9V_{CC}$

EM74HC20; EM74HCT20

Dual 4-input NAND gate



Test data is given in Table 9.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

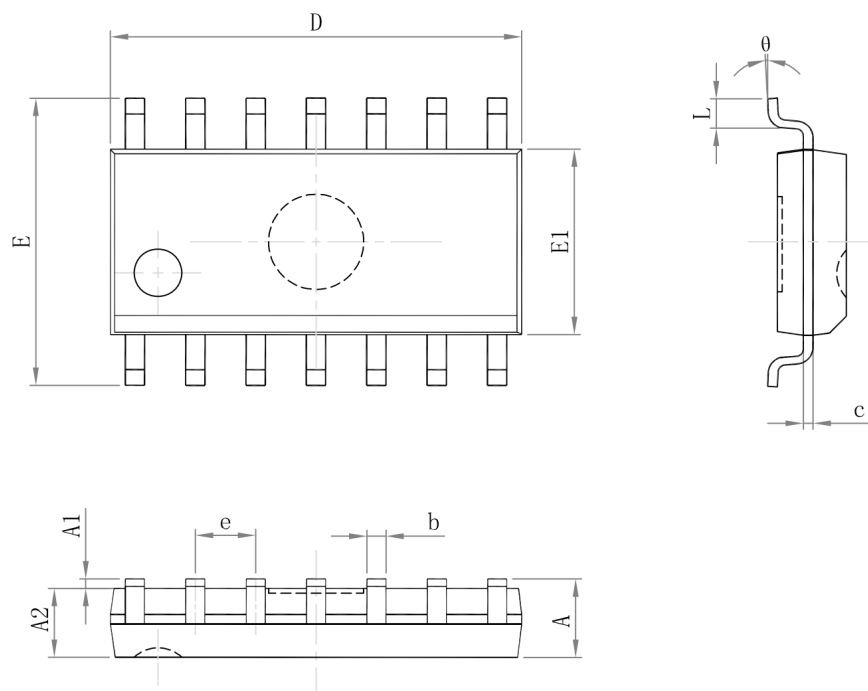
Fig. 6. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load		V_{EXT}
	V_I	$t_r = t_f$	C_L	R_L	t_{PLH}, t_{PHL}
EM74HC20	V_{CC}	≤ 2.5 ns	15 pF	500 Ω	open
EM74HCT20	3 V	≤ 2.5 ns	15 pF	500 Ω	open

11. Package Outline

SOP-14L

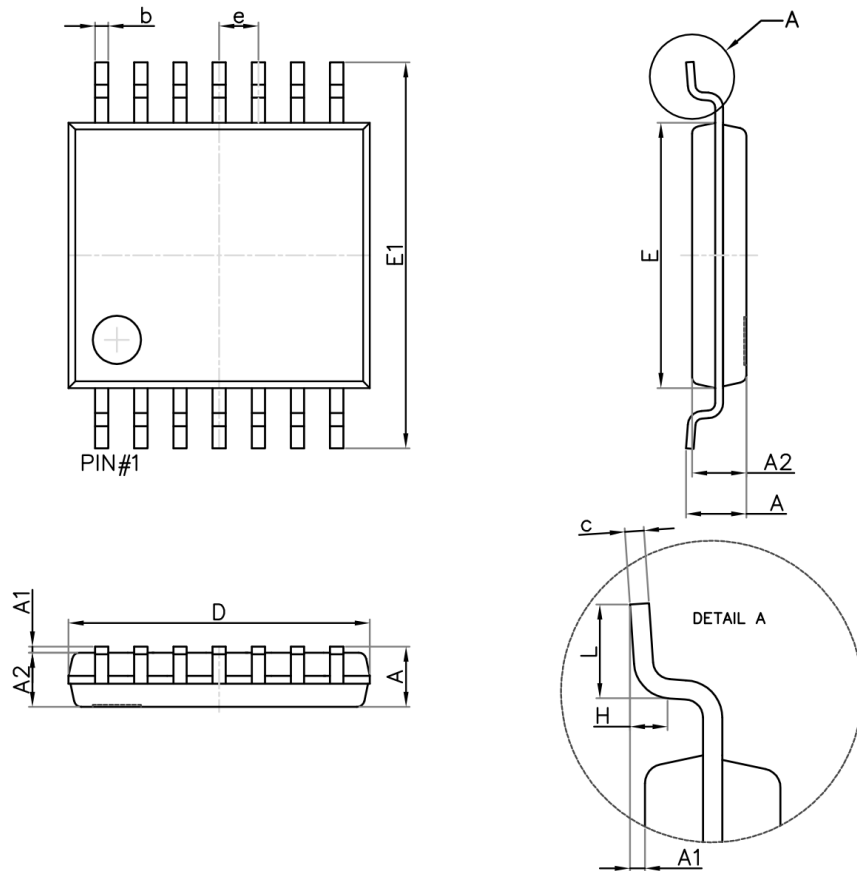


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	—	1.750	—	0.069
A1	0.100	0.250	0.004	0.010
A2	1.250	—	0.049	—
b	0.310	0.510	0.012	0.020
c	0.100	0.250	0.004	0.010
D	8.450	8.850	0.333	0.348
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

EM74HC20; EM74HCT20

Dual 4-input NAND gate

TSSOP-14L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
D	4.900	5.100	0.193	0.201
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
c	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
A	—	1.200	—	0.047
A2	0.800	1.000	0.031	0.039
A1	0.050	0.150	0.002	0.006
e	0.65 (BSC)		0.026 (BSC)	
L	0.500	0.700	0.020	0.028
H	0.25(TYP)		0.01(TYP)	
θ	1°	7°	1°	7°

12. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
CDM	Charged Device Model
TTL	Transistor-Transistor Logic

13. Revision History

Table 11. Revision history

Document ID	Release Date	Data sheet status	Change notice	Supersedes
EM74HC_HCT20 Rev. 1.0	Aug 30, 2024	Product datasheet		